

## 1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a ITO220 package intended for use in applications requiring good bidirectional blocking voltage and high surge current capability and high junction temperature capability ( $T_{j(max)} = 150\text{ °C}$ ).

## 2. Features and benefits

- High junction operating temperature capability ( $T_{j(max)} = 150\text{ °C}$ )
- High bidirectional blocking voltage capability
- Very high current surge capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Internally insulated package
- Isolated mounting base with 2500 V<sub>(RMS)</sub> isolation

## 3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

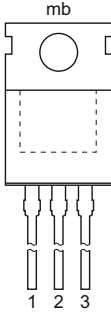

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 118\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	16	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	188	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$	-	-	207	A
$T_j$	junction temperature		-	-	150	°C
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	5	-	10	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	40	mA
$V_T$	on-state voltage	$I_T = 16\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	-	1.6	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_j = 150\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	400	-	-	V/ $\mu$ s

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN16Y-600CTF	IITO220	TYN16Y-600CTFQ	Tube	50	SOT78D	10-July-2007

## 7. Marking

Table 4. Marking codes

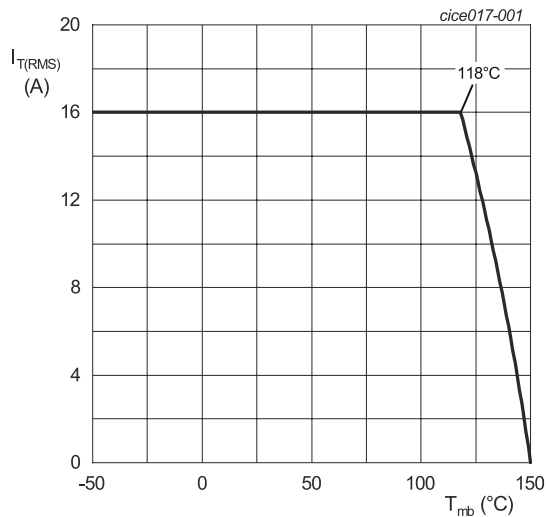
Type number	Marking codes
TYN16Y-600CTF	TYN16Y 600CTF

## 8. Limiting values

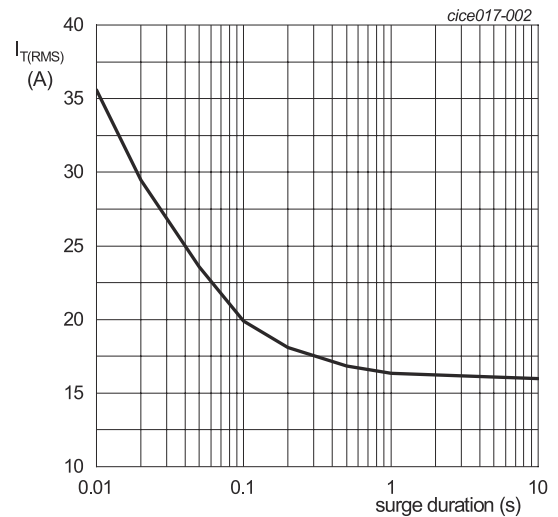
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 118\text{ }^{\circ}\text{C}$ ;	-	10.2	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 118\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	16	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	188	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 8.3\text{ ms}$	-	207	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	177	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_G = 20\text{ mA}$	-	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		-	4	A
$V_{GM}$	peak gate voltage		-	5	V
$P_{GM}$	peak gate power		-	10	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}\text{C}$
$T_j$	junction temperature		-	150	$^{\circ}\text{C}$

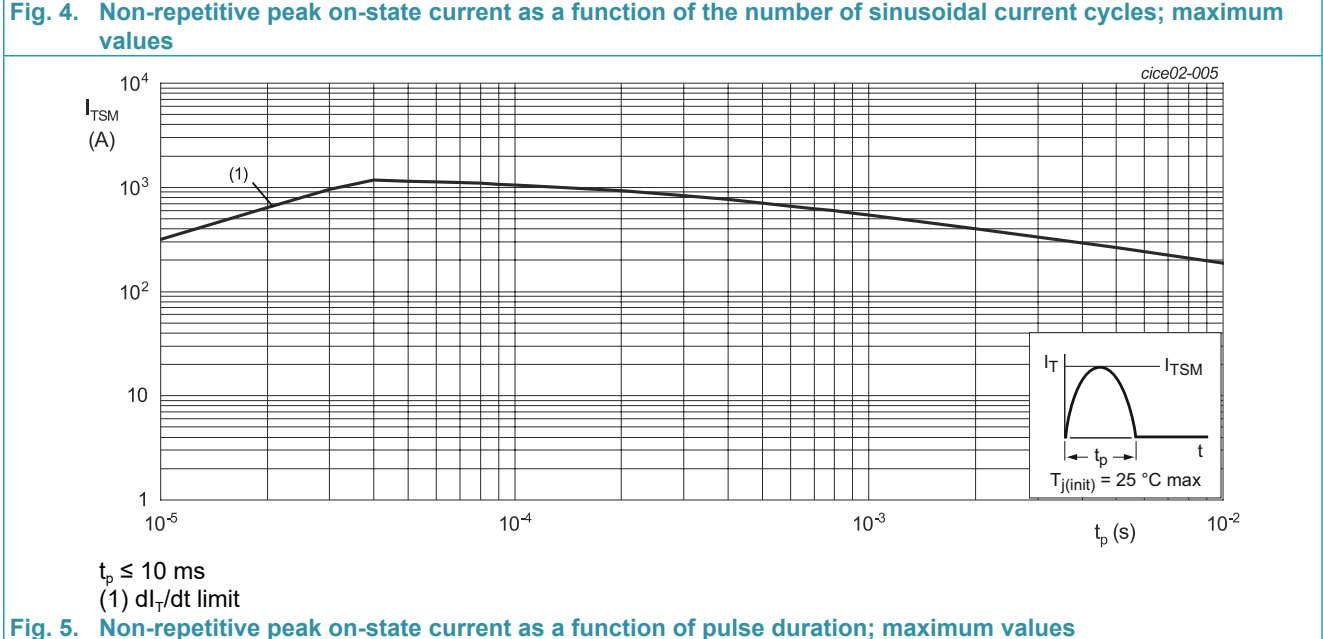
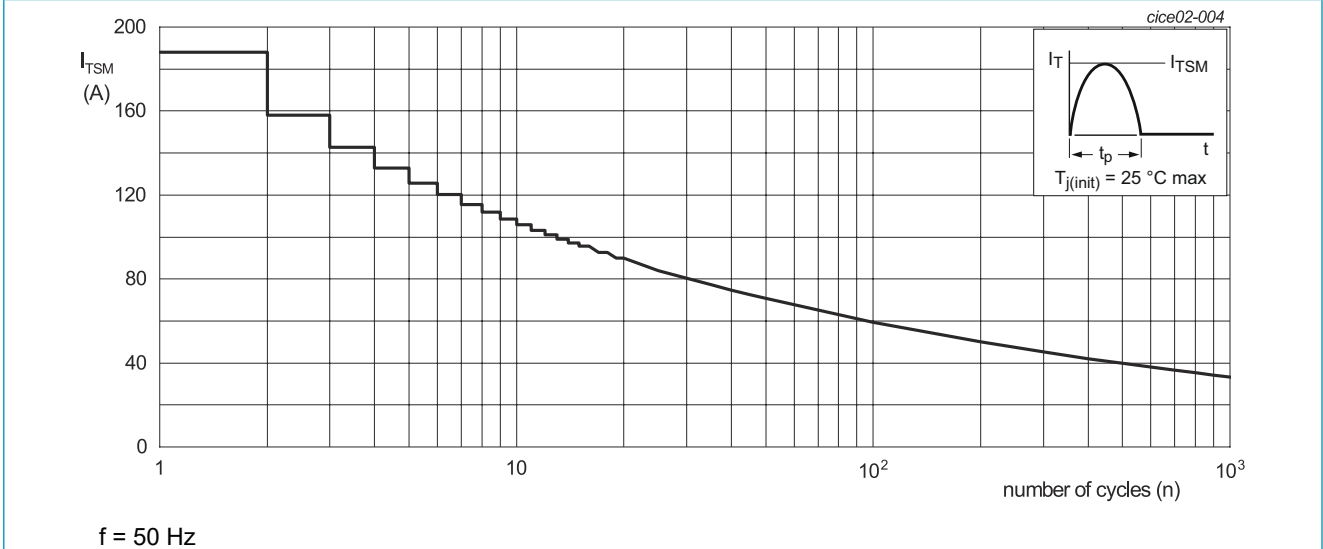
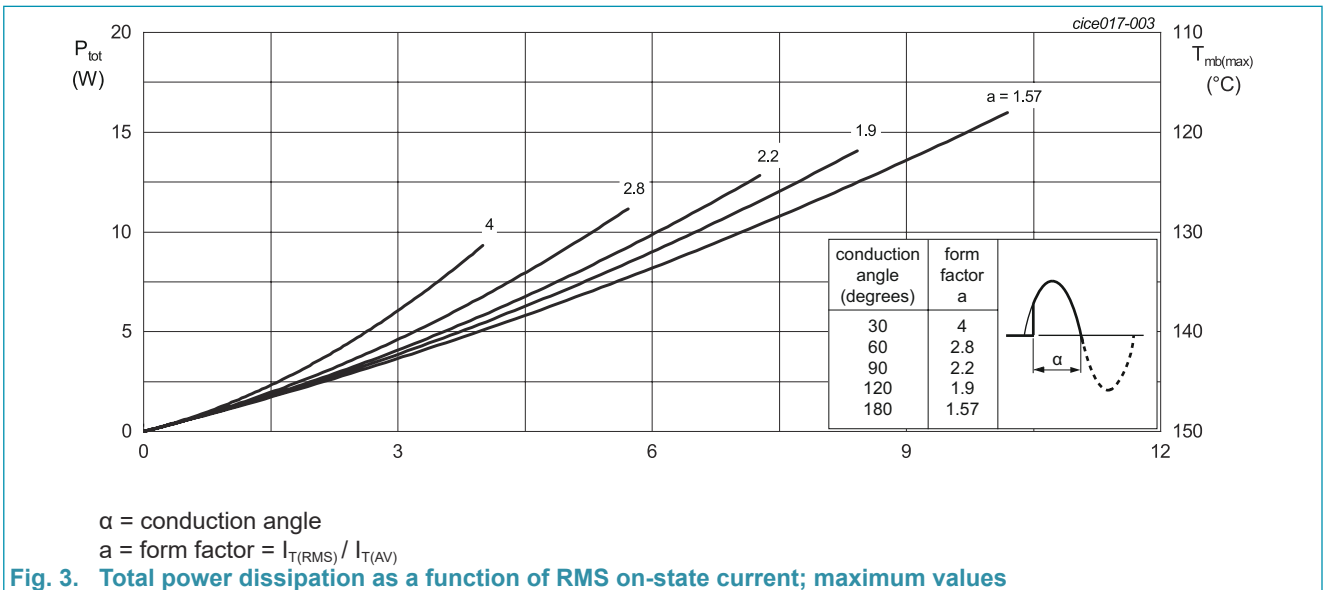


**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{mb} = 118\text{ }^{\circ}\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**



## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 6</a>	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

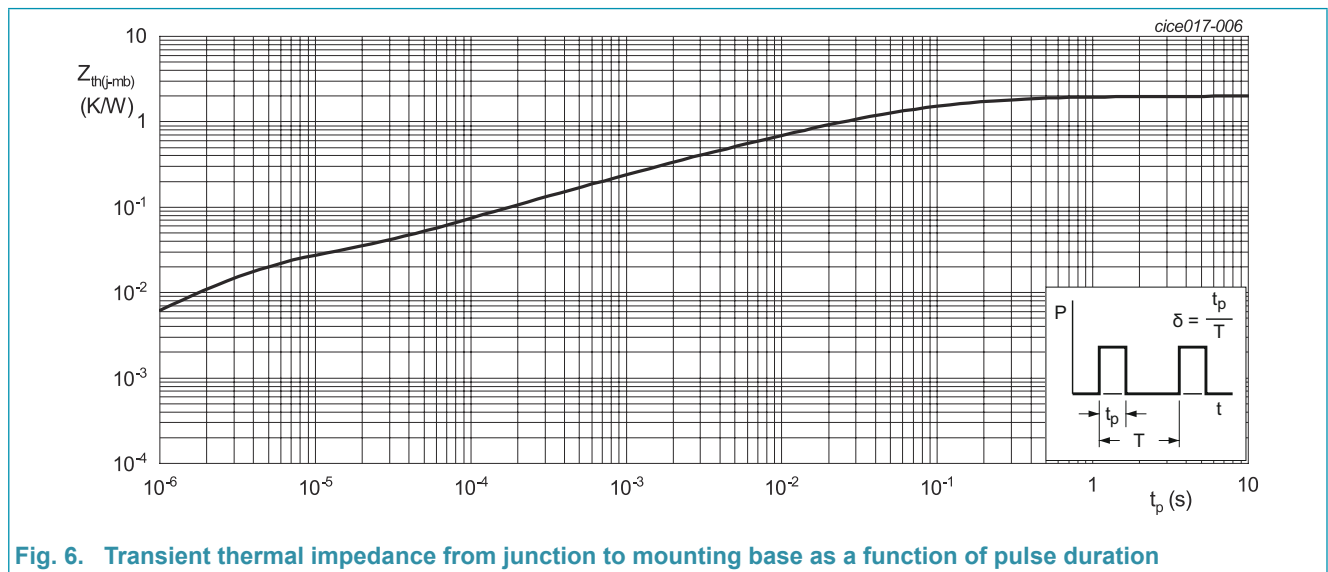


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
$C_{isol}$	isolation capacitance	from cathode to external heatsink	-	10	-	pF

## 11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7	5	-	10	mA
$I_L$	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$ ; Fig. 8	-	-	60	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C}$ ; Fig. 9	-	-	40	mA
$V_T$	on-state voltage	$I_T = 16\text{ A}; T_j = 25\text{ }^\circ\text{C}$ ; Fig. 10	-	-	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$ ; Fig. 11	-	0.8	1	V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C}$	0.25	0.45	-	V
$V_{GR}$	gate reverse voltage	$I_{RG} = 100\text{ mA}$	10	-	-	V
$I_D$	off-state current	$V_D = 600\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	10	$\mu\text{A}$
		$V_D = 600\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	-	2	mA
$I_R$	reverse current	$V_D = 600\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	10	$\mu\text{A}$
		$V_D = 600\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	-	2	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}; T_j = 150\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	400	-	-	V/ $\mu\text{s}$
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 16\text{ A}; V_D = 600\text{ V}; I_G = 20\text{ mA}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}$	-	2	-	$\mu\text{s}$
$t_q$	commutated turn-off time	$I_{TM} = 2\text{ A}; t_p = 50\text{ } \mu\text{s}; dV/dt = 5\text{ V}/\mu\text{s}; dI/dt = 30\text{ A}/\mu\text{s}$	-	-	12	$\mu\text{s}$

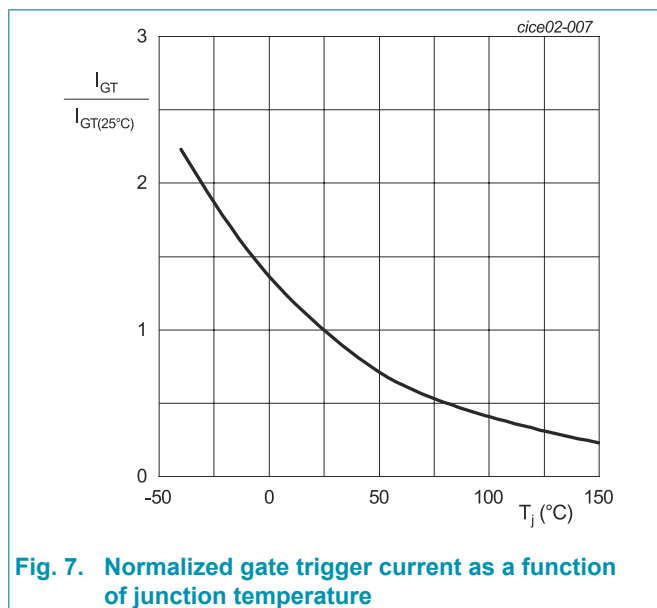


Fig. 7. Normalized gate trigger current as a function of junction temperature

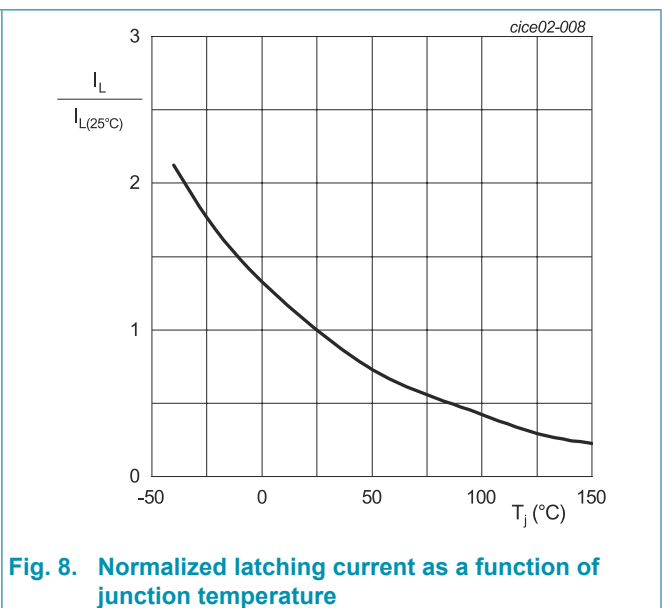
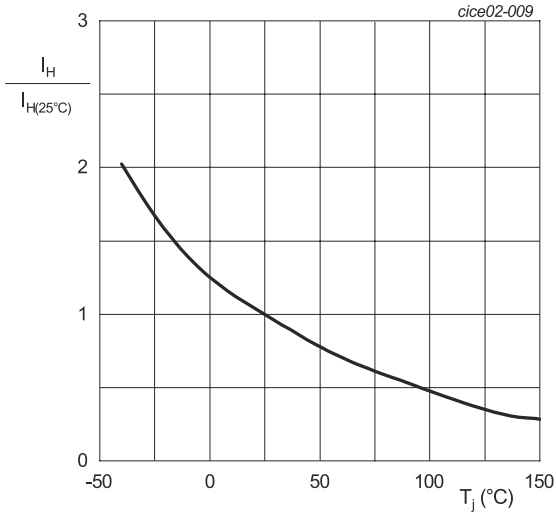
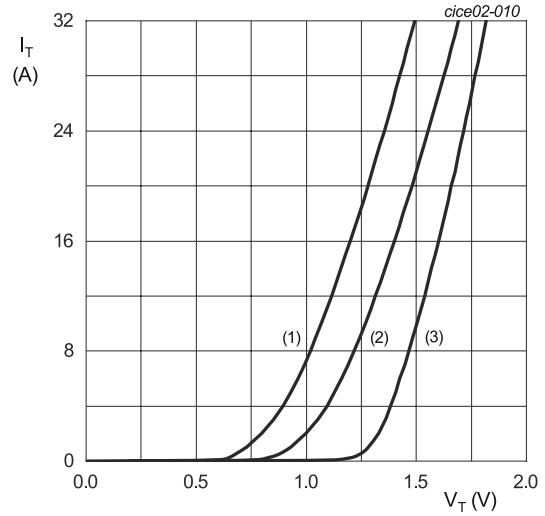


Fig. 8. Normalized latching current as a function of junction temperature

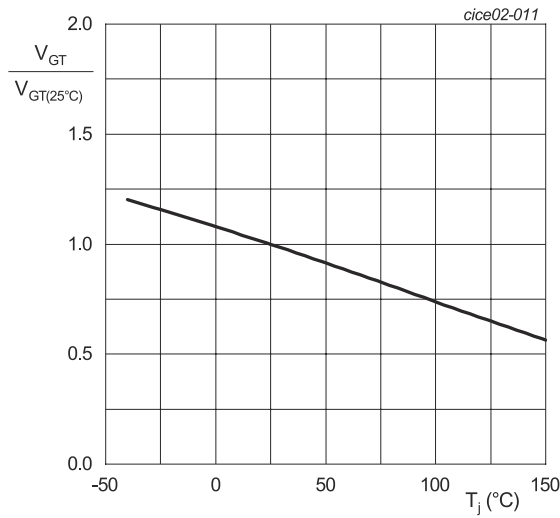


**Fig. 9. Normalized holding current as a function of junction temperature**



$V_o = 1.075 \text{ V}; R_s = 0.0196 \Omega$   
 (1)  $T_j = 150 \text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 150 \text{ }^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 10. On-state current as a function of on-state voltage**

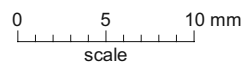
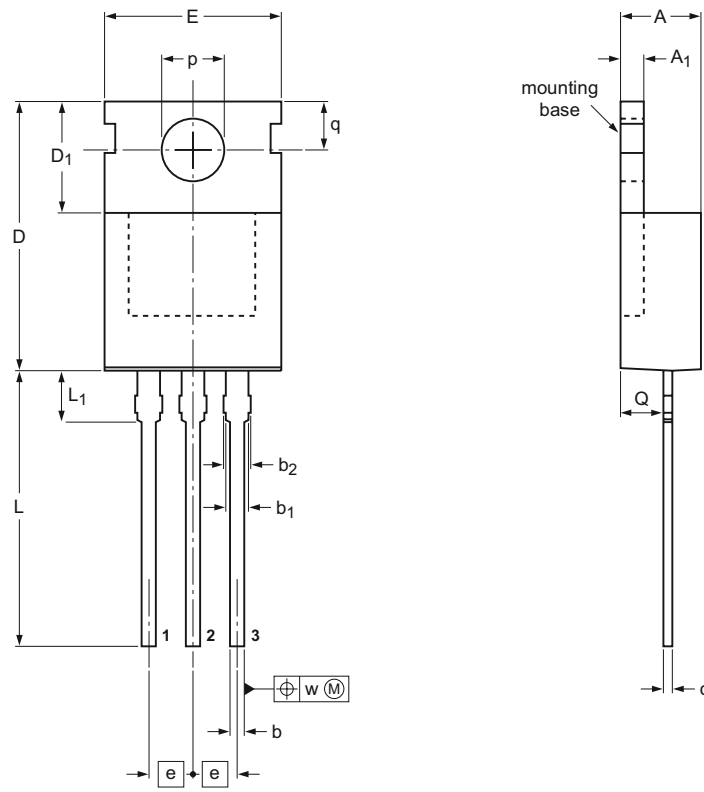


**Fig. 11. Normalized gate trigger voltage as a function of junction temperature**

## 12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220

SOT78D



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D	D <sub>1</sub> ref	E	e	L	L <sub>1</sub> ref	p	Q	q	w
mm	4.7 4.3	1.40 1.25	0.9 0.6	1.4 1.1	1.72 1.32	0.6 0.4	16.0 15.2	6.5	10.3 9.7	2.54	14.0 12.8	3.0	3.7 3.5	2.6 2.2	3.0 2.7	0.2

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78D		TO-220			07-04-04 07-07-10



## 13. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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